TPS2062-1







SLVS714A-FEBRUARY 2007-REVISED MARCH 2009

www.ti.com

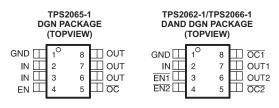
# **CURRENT-LIMITED, POWER-DISTRIBUTION SWITCHES**

#### **FEATURES**

- Output Discharge Function
- 70-mΩ High-Side MOSFET
- 1-A Continuous Current
- Thermal and Short-Circuit Protection
- Accurate Current Limit (1.1 A min, 1.9 A max)
- Operating Range: 2.7 V to 5.5 V
- 0.6-ms Typical Rise Time
- Undervoltage Lockout
- Deglitched Fault Report (OC)
- No OC Glitch During Power Up
- 1-A Maximum Standby Supply Current
- Ambient Temperature Range: -40°C to 85°C
- ESD Protection

#### **APPLICATIONS**

- Heavy Capacitive Loads
- Short-Circuit Protections



### **DESCRIPTION**

The TPS206x-1 power-distribution switches are intended for applications where heavy capacitive loads and short-circuits are likely to be encountered. This device incorporates  $70\text{-}m\Omega$  N-channel MOSFET power switches for power-distribution systems that require multiple power switches in a single package. Each switch is controlled by a logic enable input. Gate drive is provided by an internal charge pump designed to control the power-switch rise times and fall times to minimize current surges during switching. The charge pump requires no external components and allows operation from supplies as low as 2.7 V.

These switches provide a discharge function that provides a controlled discharge of the output voltage stored on the output capacitor.

When the output load exceeds the current-limit threshold or a short is present, the device limits the output current to a safe level by switching into a constant-current mode, pulling the overcurrent ( $\overline{OCx}$ ) logic output low. When continuous heavy overloads and short-circuits increase the power dissipation in the switch, causing the junction temperature to rise, a thermal protection circuit shuts off the switch to prevent damage. Recovery from a thermal shutdown is automatic once the device has cooled sufficiently. Internal circuitry ensures that the switch remains off until valid input voltage is present. This power-distribution switch is designed to set current limit at 1.5 A typically.

				GENERAL S	WITCH CATALO	G		
33 mΩ, single	TPS201xA TPS202x TPS203x	0.2 A – 2 A 0.2 A – 2 A 0.2 A – 2 A		TPS2042B 500 mA TPS2052B 500 mA TPS2046 250 mA TPS2056 250 mA TPS2062 1 A TPS2066 1 A TPS2060 1.5 A TPS2064 1.5 A	80 mΩ, dual	80 mΩ, triple	80 mΩ, quad	80 mΩ, quad
80 mΩ, single	TPS2014 TPS2015 TPS2041B TPS2051B TPS2045 TPS2045 TPS2061 TPS2065	600 mA 1 A 500 mA 500 mA 250 mA 250 mA 1 A	260 mΩ IN1 OUT 1.3 Ω	TPS2100/1 IN1 500 mA IN2 10 mA TPS2102/3/4/5 IN1 500 mA IN2 100 mA	TPS2082 500 mA TPS2090 250 mA TPS2091 250 mA TPS2092 250 mA	TPS2053B 500 mA TPS2047 250 mA TPS2057 250 mA	TPS2044B 500 mA TPS2054B 500 mA	TPS2085 500 mA TPS2086 500 mA TPS2087 500 mA TPS2095 250 mA TPS2096 250 mA TPS2097 250 mA



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### AVAILABLE OPTION AND ORDERING INFORMATION<sup>(1)</sup>

TA	ENABLE	RECOMMENDED MAXIMUM	TYPICAL SHORT-CIRCUIT	NUMBER OF		KAGED ICES <sup>(2)</sup>	
'A		CONTINUOUS LOAD CURRENT	CURRENT LIMIT AT 25°C	SWITCHES	MSOP (DGN)	SOIC(D)	
	Active high			Single	TPS2065DGN-1		
-40°C to 85°C	Active low	1 A	1.5 A	Dual		TPS2062D-1	
	Active high			Dual	TPS2066DGN-1		

<sup>(1)</sup> For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

#### **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range unless otherwise noted (1)

		UNIT		
Input voltage range, V <sub>I(IN)</sub> (2)		−0.3 V to 6 V		
Output voltage range, V <sub>O(OUT)</sub> (2), V <sub>O(OUTx)</sub>		-0.3 V to 6 V		
Input voltage range, $V_{I(\overline{EN})}$ , $V_{I(EN)}$ , $V_{I(\overline{ENx})}$ , $V_{I(\overline{I})}$	-0.3 V to 6 V			
Voltage range, $V_{I(\overline{OC})}$ , $V_{I(\overline{OCx})}$	-0.3 V to 6 V			
Continuous output current, I <sub>O(OUT)</sub> , I <sub>O(OUTx)</sub>		Internally limited		
Continuous total power dissipation		See Dissipation Rating Table		
Operating virtual junction temperature range	, T <sub>J</sub>	-40°C to 125°C		
Storage temperature range, T <sub>stg</sub>		−65°C to 150°C		
Flantanetation disable ways (FCD) and to ation	Human body model MIL-STD-883C	2 kV		
Electrostatic discharge (ESD) protection	Charge device model (CDM)	500 V		

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to GND.

<sup>(2)</sup> The package is available taped and reeled. Add an R suffix to device types (e.g., TPS2062-1DR).



#### **DISSIPATING RATING TABLE**

PACKAGE	T <sub>A</sub> ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 70°C POWER RATING	T <sub>A</sub> = 85°C POWER RATING
D-8	585.82 mW	5.8582 mW/°C	322.20 mW	234.32 mW
DGN-8	1712.3 mW	17.123 mW/°C	941.78 mW	684.33 mW

#### RECOMMENDED OPERATING CONDITIONS

	MIN	MAX	UNIT
Input voltage, V <sub>I(IN)</sub>	2.7	5.5	V
Input voltage, $V_{I(\overline{EN})}$ , $V_{I(\overline{ENx})}$ , $V_{I(\overline{ENx})}$ , $V_{I(ENx)}$	0	5.5	V
Continuous output current, I <sub>O(OUT)</sub> , I <sub>O(OUTx)</sub>	0	1	А
Steady state current through discharge. Device disabled, measured through output pin(s)		8	mA
Operating virtual junction temperature, T <sub>J</sub>	-40	125	°C

### **ELECTRICAL CHARACTERISTICS**

over recommended operating junction temperature range,  $V_{I(IN)} = 5.5 \text{ V}$ ,  $I_O = 1 \text{ A}$ ,  $V_{I(/ENx)} = 0 \text{ V}$ , or  $V_{I(ENx)} = 5.5 \text{ V}$  (unless otherwise noted)

	PARAMETER		MIN	TYP	MAX	UNIT		
POWER S	SWITCH							
	Static drain-source on-state resistance, 5-V operation and 3.3-V operation	V <sub>I(IN)</sub> = 5 V or 3.3	V, I <sub>O</sub> = 1 A, -40°C ≤ T <sub>J</sub> ≤	125°C		70	135	mΩ
r <sub>DS(on)</sub>	Static drain-source on-state resistance, 2.7-V operation (2)	V <sub>I(IN)</sub> = 2.7 V, I <sub>O</sub> =	= 1 A, -40°C ≤ T <sub>J</sub> ≤ 125°C	I A, -40°C ≤ T <sub>J</sub> ≤ 125°C				mΩ
t <sub>r</sub> (2)	D: .:	. V <sub>I(IN)</sub> = 5.5 V				0.6	1.5	
t <sub>r</sub> (2)	Rise time, output	V <sub>I(IN)</sub> = 2.7 V				0.4	1	
. (2)	F. II.	V <sub>I(IN)</sub> = 5.5 V	$C_L = 1 \mu F, R_L = 5 \Omega,$	I <sub>J</sub> = 25°C	0.05		0.5	ms
t <sub>f</sub> (2)	Fall time, output	V <sub>I(IN)</sub> = 2.7 V			0.05		0.5	
ENABLE	INPUT EN OR EN	1	<u>'</u>				'	
V <sub>IH</sub>	High-level input voltage	2.7 V ≤ V <sub>I(IN)</sub> ≤5.5	V		2			V
V <sub>IL</sub>	Low-level input voltage	$2.7 \text{ V} \le \text{V}_{\text{I(IN)}} \le 5.5$	5 V				0.8	V
I	Input current	$V_{I(\overline{ENx})} = 0 \text{ V or } 5.5$	-0.5		0.5	μΑ		
t <sub>on</sub> (3)	Turnon time	$C_L = 100  \mu F,  R_L = 5  \Omega$					3	
t <sub>off</sub> (3)	Turnoff time $C_L = 100 \ \mu F, \ R_L = 5 \ \Omega$						10	ms
CURREN	T LIMIT							
	Chart aircuit autaut aurrant	$V_{I(IN)} = 5 \text{ V}$ , OUT connected to GND, $T_J = 25^{\circ}\text{C}$			1.1	1.5	1.9	Α
I <sub>OS</sub>	Short-circuit output current	device enabled in	to short-circuit	-40°C ≤ T <sub>J</sub> ≤ 125°C	1.1	1.5	2.1	
I <sub>OC_TRIP</sub> (3)	Overcurrent trip threshold	V <sub>I(IN)</sub> = 5 V, current ramp (≤ 100 A/s) on OUT				2.4	3	Α
SUPPLY	CURRENT (TPS2065-1)							
Cupply au	umant law laval autout	No load on OUT,	$V_{I(\overline{ENx})} = 5.5 \text{ V},$	T <sub>J</sub> = 25°C		0.5	1	
Supply cu	urrent, low-level output	or $V_{I(ENx)} = 0 V$	(=:)	-40°C ≤ T <sub>J</sub> ≤ 125°C		0.5	10	μА
Cupply ou	urrent, high-level output	No load on OUT,	$V_{I(\overline{ENx})} = 0 \text{ V},$	T <sub>J</sub> = 25°C		43	60	
Supply cu	arrent, nign-iever output	or $V_{I(ENx)} = 5.5 \text{ V}$	,	-40°C ≤ T <sub>J</sub> ≤ 125°C		43	70	μΑ
Reverse le	leakage current	V <sub>I(OUTx)</sub> = 5.5 V, II	N = ground <sup>(3)</sup>	T <sub>J</sub> = 25°C		0		μΑ
SUPPLY	CURRENT (TPS2062-1, TPS2066-1)							
Supply current, low-level output		No load on OUT,	$V_{I(\overline{ENx})} = 5.5 \text{ V},$	$T_J = 25^{\circ}C$		0.5	1	
		or $V_{I(ENx)} = 0 V$		-40°C ≤ T <sub>J</sub> ≤ 125°C		0.5	20	μΑ
Supply ou	urrent, high-level output	No load on OUT,	$V_{I(\overline{ENx})} = 0 V,$	T <sub>J</sub> = 25°C		50	70	μA
Зирріу си	arient, mgirievei output			-40°C ≤ T <sub>J</sub> ≤ 125°C		50	90	μΑ
Reverse I	leakage current	$V_{I(OUTx)} = 5.5 \text{ V}, IN = ground^{(3)}$ $T_J = 25^{\circ}C$				0.2		μΑ

<sup>(1)</sup> Pulse-testing techniques maintain junction temperature close to ambient temperature; thermal effects must be taken into account separately.

<sup>(2)</sup> Not tested in production, specified by design.

<sup>(3)</sup> Not tested in production, specified by design.



## **ELECTRICAL CHARACTERISTICS (continued)**

over recommended operating junction temperature range,  $V_{I(IN)} = 5.5 \text{ V}$ ,  $I_O = 1 \text{ A}$ ,  $V_{I(/ENx)} = 0 \text{ V}$ , or  $V_{I(ENx)} = 5.5 \text{ V}$  (unless otherwise noted)

PARAMETER	TEST CONDITIONS <sup>(1)</sup>	MIN	TYP	MAX	UNIT
UNDERVOLTAGE LOCKOUT					
Low-level input voltage, IN		2		2.5	V
Hysteresis, IN	T <sub>J</sub> = 25°C		75		mV
OVERCURRENT OC1 and OC2					
Output low voltage, V <sub>OL(OCx)</sub>	$I_{O(\overline{OCx})} = 5 \text{ mA}$			0.4	V
Off-state current <sup>(4)</sup>	$V_{O(\overline{OCx})} = 5 \text{ V or } 3.3 \text{ V}$			1	μΑ
OC deglitch <sup>(4)</sup>	OCx assertion or deassertion	4	8	15	ms
Discharge resistance	V <sub>CC</sub> = 5 V, disabled, I <sub>O</sub> = 1 mA		100		Ω
THERMAL SHUTDOWN (5)					
Thermal shutdown threshold <sup>(4)</sup>		135			°C
Recovery from thermal shutdown <sup>(4)</sup>		125			°C
Hysteresis <sup>(4)</sup>			10		°C

<sup>(4)</sup> Not tested in production, specified by design.

#### **DEVICE INFORMATION**

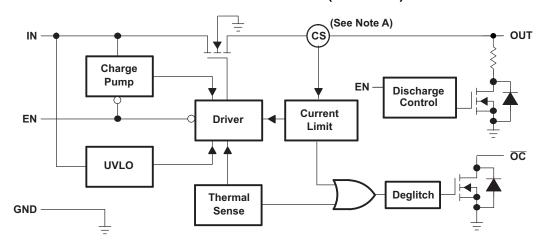
#### **Pin Functions**

	PIN				DESCRIPTION				
NAME	TPS2065-1	TPS2062-1	TPS2066-1	1/0	DESCRIPTION				
EN	4	_	_	I	Enable input, logic high turns on power switch				
EN1	-	3	_	ı	Enable input, logic low turns on channel 1				
EN <sub>2</sub>	-	4	_	- 1	Enable input, logic high turns on channel 2				
EN1	-	-	3	- 1	Enable input, logic high turns on channel 1				
EN2	-	-	4	- 1	Enable input, logic high turns on channel 2				
GND	1	1	1		Ground connection				
IN	2, 3	2	2	I	Input voltage; connect a 0.1 $\mu\text{F}$ or greater ceramic capacitor from IN to GND as close to the IC as possible				
OC	5	_	_	0	Active-low open-drain output, asserted during over-current				
OC1	-	8	8	0	Active-low open-drain output, asserted during over-current for channel 1				
OC2		5	5	0	Active-low open-drain output, asserted during over-current for channel 2				
OUT	6, 7, 8	_	_	0	Power-switch output				
OUT1	-	7	7	0	Power-switch output for channel 1				
OUT2	-	6	6	0	Power-switch output for channel 2				

<sup>(5)</sup> The thermal shutdown only reacts under overcurrent conditions.

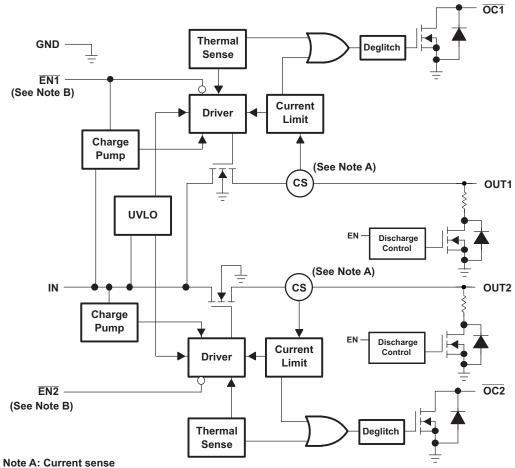


## **FUNCTIONAL BLOCK DIAGRAM (TPS2065-1)**



Note A: Current sense

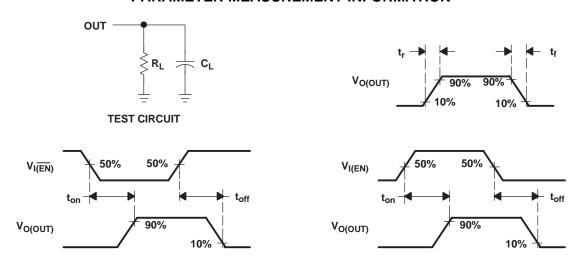
## FUNCTIONAL BLOCK DIAGRAM (TPS2062-1 and TPS2066-1)



Note B: Active low (ENx) for TPS2062. Active high (ENx) for TPS2066



### PARAMETER MEASUREMENT INFORMATION



**VOLTAGE WAVEFORMS** 

Figure 1. Test Circuit and Voltage Waveforms

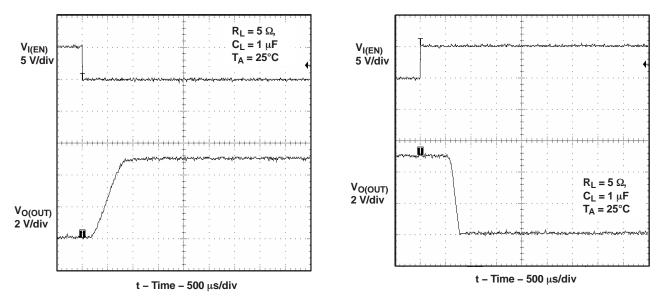
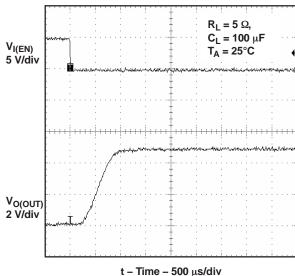


Figure 2. Turnon Delay and Rise Time With 1-µF Load

Figure 3. Turnoff Delay and Fall Time With 1-µF Load



## PARAMETER MEASUREMENT INFORMATION (continued)



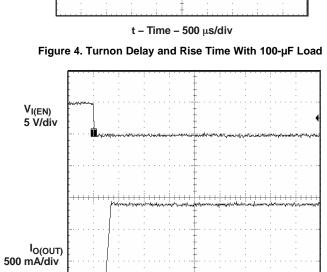


Figure 6. Short-Circuit Current, Device Enabled Into Short

t – Time – 500  $\mu$ s/div

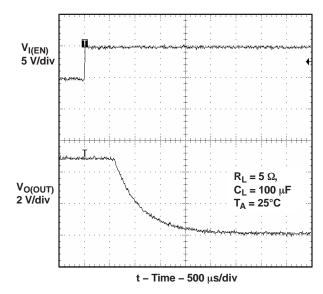


Figure 5. Turnoff Delay and Fall Time With 100-µF Load

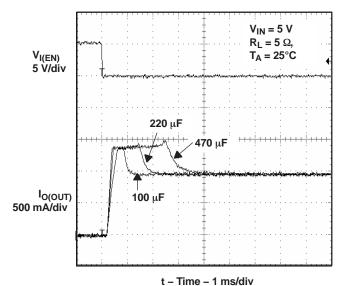


Figure 7. Inrush Current With Different Load Capacitance



# PARAMETER MEASUREMENT INFORMATION (continued)

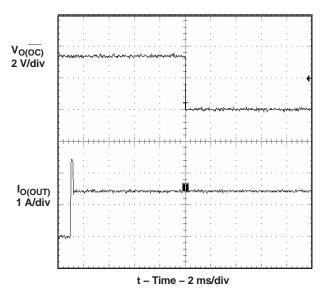


Figure 8. 2-Ω Load Connected to Enabled Device

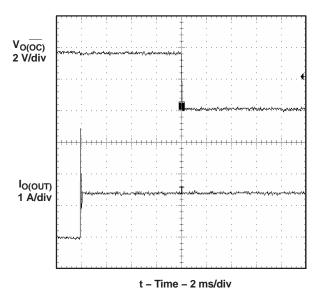
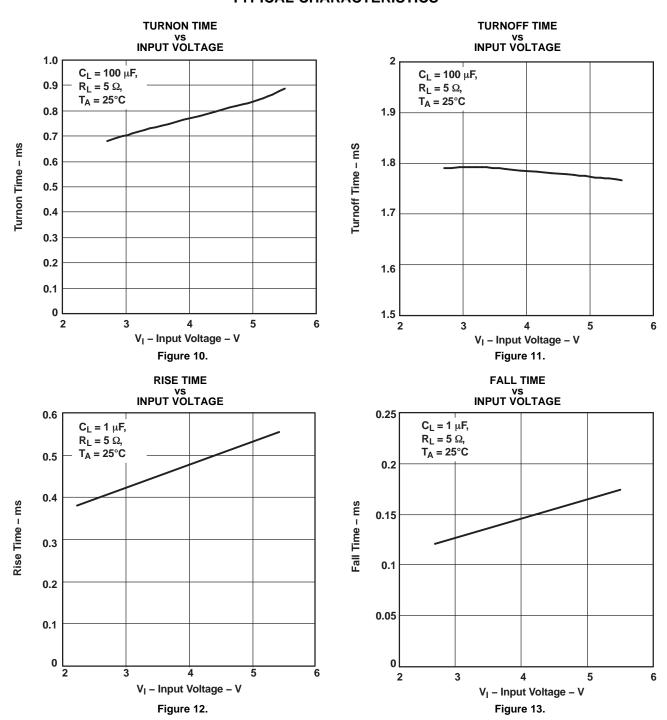


Figure 9. 1- $\Omega$  Load Connected to Enabled Device

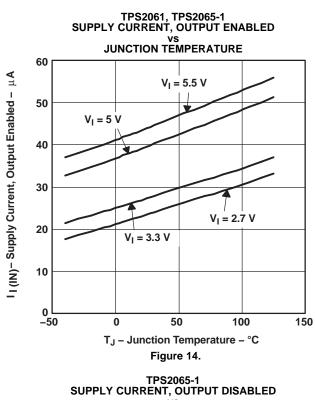


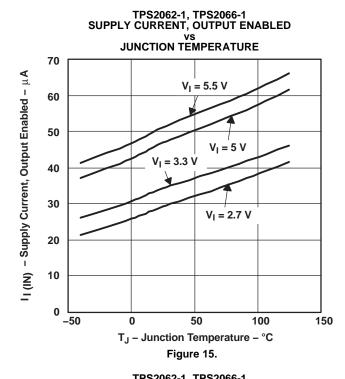
## TYPICAL CHARACTERISTICS

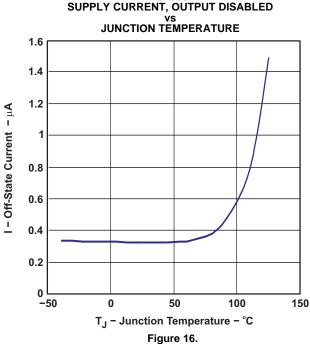


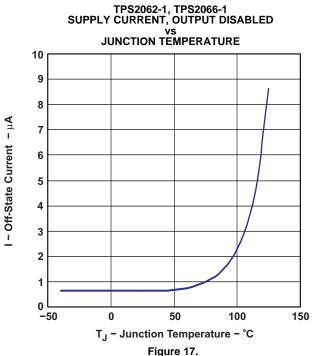


## **TYPICAL CHARACTERISTICS (continued)**



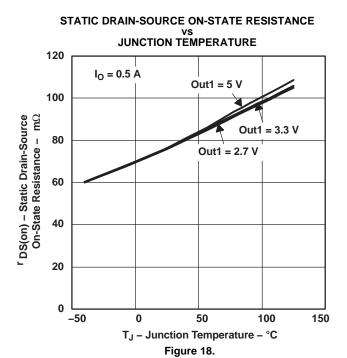


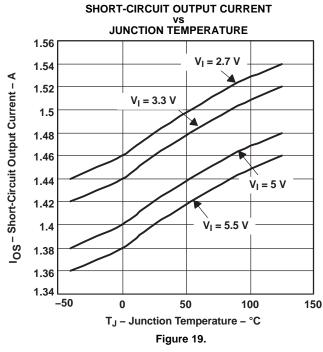


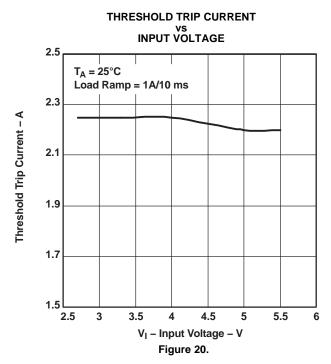


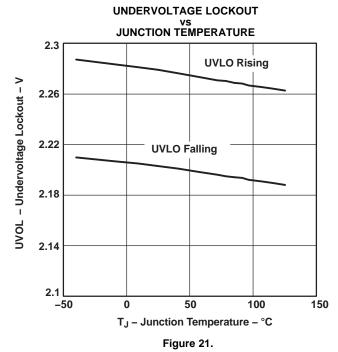


## **TYPICAL CHARACTERISTICS (continued)**



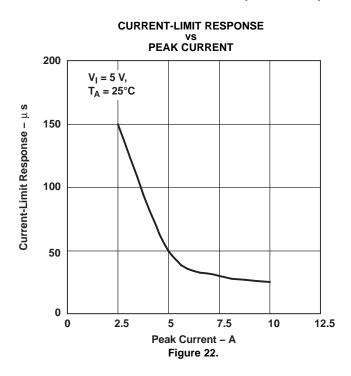








# **TYPICAL CHARACTERISTICS (continued)**





#### APPLICATION INFORMATION

#### **POWER-SUPPLY CONSIDERATIONS**

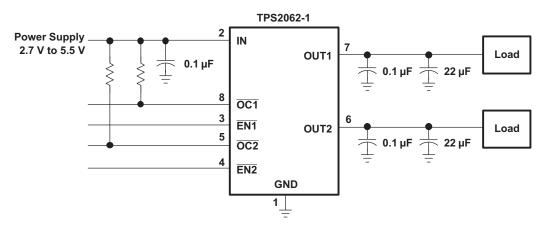


Figure 23. Typical Application

A 0.01- $\mu$ F to 0.1- $\mu$ F ceramic bypass capacitor between IN and GND, close to the device, is recommended. Placing a high-value electrolytic capacitor on the output pin(s) is recommended when the output load is heavy. This precaution reduces power-supply transients that may cause ringing on the input. Additionally, bypassing the output with a 0.01- $\mu$ F to 0.1- $\mu$ F ceramic capacitor improves the immunity of the device to short-circuit transients.

#### **OVERCURRENT**

A sense FET is employed to check for overcurrent conditions. Unlike current-sense resistors, sense FETs do not increase the series resistance of the current path. When an overcurrent condition is detected, the device maintains a constant output current and reduces the output voltage accordingly. Complete shutdown occurs only if the fault is present long enough to activate thermal limiting.

Three possible overload conditions can occur. In the first condition, the output has been shorted before the device is enabled or before  $V_{I(IN)}$  has been applied (see Figure 15). The TPS206x-1 senses the short and immediately switches into a constant-current output.

In the second condition, a short or an overload occurs while the device is enabled. At the instant the overload occurs, high currents may flow for a short period of time before the current-limit circuit can react. After the current-limit circuit has tripped (reached the overcurrent trip threshold), the device switches into constant-current mode.

In the third condition, the load has been gradually increased beyond the recommended operating current. The current is permitted to rise until the current-limit threshold is reached or until the thermal limit of the device is exceeded (see Figure 17). The TPS206x-1 is capable of delivering current up to the current-limit threshold without damaging the device. Once the threshold has been reached, the device switches into its constant-current mode.

#### **OC RESPONSE**

The  $\overline{\text{OCx}}$  open-drain output is asserted (active low) when an overcurrent or overtemperature shutdown condition is encountered after a 10-ms deglitch timeout. The output remains asserted until the overcurrent or overtemperature condition is removed. Connecting a heavy capacitive load to an enabled device can cause a momentary overcurrent condition; however, no false reporting on  $\overline{\text{OCx}}$  occurs due to the 10-ms deglitch circuit. The TPS206x-1 is designed to eliminate false overcurrent reporting. The internal overcurrent deglitch eliminates the need for external components to remove unwanted pulses.  $\overline{\text{OCx}}$  is not deglitched when the switch is turned off due to an overtemperature shutdown.

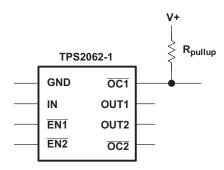


Figure 24. Typical Circuit for the OC Pin

#### POWER DISSIPATION AND JUNCTION TEMPERATURE

The low on-resistance on the N-channel MOSFET allows the small surface-mount packages to pass large currents. The thermal resistances of these packages are high compared to those of power packages; it is good design practice to check power dissipation and junction temperature. Begin by determining the  $r_{DS(on)}$  of the N-channel MOSFET relative to the input voltage and operating temperature. As an initial estimate, use the highest operating ambient temperature of interest and read  $r_{DS(on)}$  from Figure 18. Using this value, the power dissipation per switch can be calculated by:

$$P_D = r_{DS(on)} \times I^2$$

Multiply this number by the number of switches being used. This step renders the total power dissipation from the N-channel MOSFETs.

Finally, calculate the junction temperature:

$$T_J = P_D \times R_{\theta JA} + T_A$$

Where:

T<sub>A</sub>= Ambient temperature °C

 $R_{\theta,JA}$  = Thermal resistance

P<sub>D</sub> = Total power dissipation based on number of switches being used.

Compare the calculated junction temperature with the initial estimate. If they do not agree within a few degrees, repeat the calculation, using the calculated value as the new estimate. Two or three iterations are generally sufficient to get a reasonable answer.

## THERMAL PROTECTION

Thermal protection prevents damage to the IC when heavy-overload or short-circuit faults are present for extended periods of time. The TPS206x-1 implements a thermal sensing to monitor the operating junction temperature of the power distribution switch. In an overcurrent or short-circuit condition, the junction temperature rises due to excessive power dissipation. Once the die temperature rises to approximately 140°C due to overcurrent conditions, the internal thermal sense circuitry turns the power switch off, thus preventing the power switch from damage. Hysteresis is built into the thermal sense circuit, and after the device has cooled approximately 10°C, the switch turns back on. The switch continues to cycle in this manner until the load fault or input power is removed. The  $\overline{OCx}$  open-drain output is asserted (active low) when an overtemperature shutdown or overcurrent occurs.

#### **UNDERVOLTAGE LOCKOUT (UVLO)**

An undervoltage lockout ensures that the power switch is in the off state at power up. Whenever the input voltage falls below approximately 2 V, the power switch is quickly turned off. This facilitates the design of hot-insertion systems where it is not possible to turn off the power switch before input power is removed. The UVLO also keeps the switch from being turned on until the power supply has reached at least 2 V, even if the switch is enabled. On reinsertion, the power switch is turned on, with a controlled rise time to reduce EMI and voltage overshoots.



## **UNIVERSAL SERIAL BUS (USB) APPLICATIONS**

The universal serial bus (USB) interface is a 12-Mb/s, or 1.5-Mb/s, multiplexed serial bus designed for low-to-medium bandwidth PC peripherals (e.g., keyboards, printers, scanners, and mice). The four-wire USB interface is conceived for dynamic attach-detach (hot plug-unplug) of peripherals. Two lines are provided for differential data, and two lines are provided for 5-V power distribution.

USB data is a 3.3-V level signal, but power is distributed at 5 V to allow for voltage drops in cases where power is distributed through more than one hub across long cables. Each function must provide its own regulated 3.3 V from the 5-V input or its own internal power supply.

The USB specification defines the following five classes of devices, each differentiated by power-consumption requirements:

- Hosts/self-powered hubs (SPH)
- Bus-powered hubs (BPH)
- Low-power, bus-powered functions
- · High-power, bus-powered functions
- Self-powered functions

SPHs and BPHs distribute data and power to downstream functions. The TPS206x-1 has higher current capability than required by one USB port; so, it can be used on the host side and supplies power to multiple downstream ports or functions.

#### **HOST/SELF-POWERED AND BUS-POWERED HUBS**

Hosts and SPHs have a local power supply that powers the embedded functions and the downstream ports (see Figure 25). This power supply must provide from 5.25 V to 4.75 V to the board side of the downstream connection under full-load and no-load conditions. Hosts and SPHs are required to have current-limit protection and must report overcurrent conditions to the USB controller. Typical SPHs are desktop PCs, monitors, printers, and stand-alone hubs.

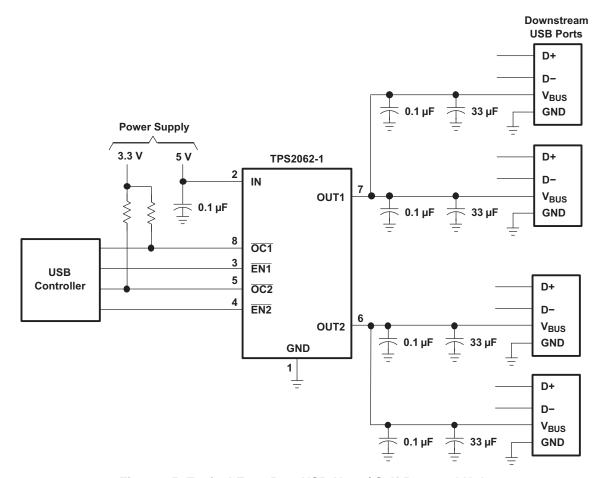


Figure 25. Typical Four-Port USB Host / Self-Powered Hub

BPHs obtain all power from upstream ports and often contain an embedded function. The hubs are required to power up with less than one unit load. The BPH usually has one embedded function, and power is always available to the controller of the hub. If the embedded function and hub require more than 100 mA on power up, the power to the embedded function may need to be kept off until enumeration is completed. This can be accomplished by removing power or by shutting off the clock to the embedded function. Power switching the embedded function is not necessary if the aggregate power draw for the function and controller is less than one unit load. The total current drawn by the bus-powered device is the sum of the current to the controller, the embedded function, and the downstream ports, and it is limited to 500 mA from an upstream port.

#### LOW-POWER BUS-POWERED AND HIGH-POWER BUS-POWERED FUNCTIONS

Both low-power and high-power bus-powered functions obtain all power from upstream ports; low-power functions always draw less than 100 mA; high-power functions must draw less than 100 mA at power up and can draw up to 500 mA after enumeration. If the load of the function is more than the parallel combination of 44  $\Omega$  and 10  $\mu$ F at power up, the device must implement inrush current limiting (see Figure 26). With TPS206x-1, the internal functions could draw more than 500 mA, which fits the needs of some applications such as motor driving circuits.



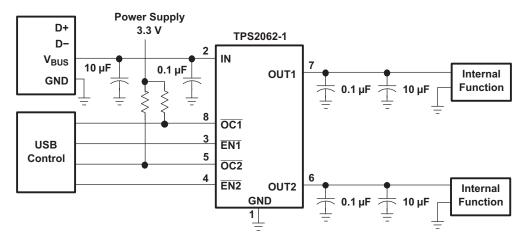


Figure 26. High-Power Bus-Powered Function

## **USB POWER-DISTRIBUTION REQUIREMENTS**

USB can be implemented in several ways, and, regardless of the type of USB device being developed, several power-distribution features must be implemented.

- Hosts/SPHs must:
  - Current-limit downstream ports
  - Report overcurrent conditions on USB V<sub>BUS</sub>
- BPHs must:
  - Enable/disable power to downstream ports
  - Power up at <100 mA</li>
  - Limit inrush current (<44 Ω and 10 μF)</li>
- Functions must:
  - Limit inrush currents
  - Power up at <100 mA

The feature set of the TPS206x-1 allows them to meet each of these requirements. The integrated current-limiting and overcurrent reporting is required by hosts and self-powered hubs. The logic-level enable and controlled rise times meet the need of both input and output ports on bus-powered hubs, as well as the input ports for bus-powered functions (see Figure 27).

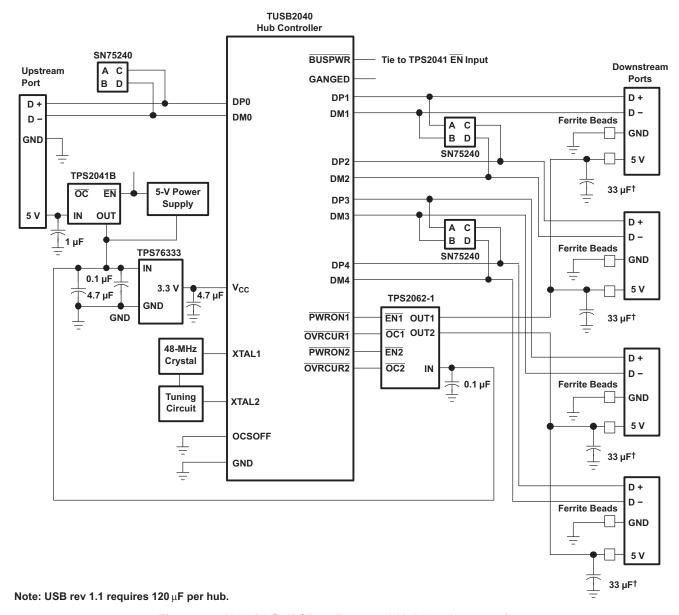


Figure 27. Hybrid Self / Bus-Powered Hub Implementation

#### **GENERIC HOT-PLUG APPLICATIONS**

In many applications it may be necessary to remove modules or pc boards while the main unit is still operating. These are considered hot-plug applications. Such implementations require the control of current surges seen by the main power supply and the card being inserted. The most effective way to control these surges is to limit and slowly ramp the current and voltage being applied to the card, similar to the way in which a power supply normally turns on. Due to the controlled rise times and fall times of the TPS206x-1, these devices can be used to provide a softer start-up to devices being hot-plugged into a powered system. The UVLO feature of the TPS206x-1 also ensures that the switch is off after the card has been removed, and that the switch is off during the next insertion. The UVLO feature insures a soft start with a controlled rise time for every insertion of the card or module.



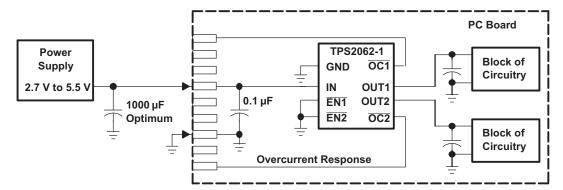


Figure 28. Typical Hot-Plug Implementation

By placing the TPS206x-1 between the  $V_{CC}$  input and the rest of the circuitry, the input power reaches these devices first after insertion. The typical rise time of the switch is approximately 1 ms, providing a slow voltage ramp at the output of the device. This implementation controls system surge currents and provides a hot-plugging mechanism for any device.

#### **DETAILED DESCRIPTION**

#### **Power Switch**

The power switch is an N-channel MOSFET with a low on-state resistance. Configured as a high-side switch, the power switch prevents current flow from OUT to IN and IN to OUT when disabled. The power switch supplies a minimum current of 1 A.

#### **Charge Pump**

An internal charge pump supplies power to the driver circuit and provides the necessary voltage to pull the gate of the MOSFET above the source. The charge pump operates from input voltages as low as 2.7 V and requires little supply current.

#### **Driver**

The driver controls the gate voltage of the power switch. To limit large current surges and reduce the associated electromagnetic interference (EMI) produced, the driver incorporates circuitry that controls the rise times and fall times of the output voltage.

## Enable (ENx or ENx)

The logic enable disables the power switch and the bias for the charge pump, driver, and other circuitry to reduce the supply current. The supply current is reduced to less than 1  $\mu$ A when a logic high is present on ENx, or when a logic low is present on ENx. A logic zero input on ENx, or a logic high input on ENx restores bias to the drive and control circuits and turns the switch on. The enable input is compatible with both TTL and CMOS logic levels.

## Overcurrent (OCx)

The  $\overline{OCx}$  open-drain output is asserted (active low) when an overcurrent or overtemperature condition is encountered. The output remains <u>asserted</u> until the overcurrent or overtemperature condition is removed. A 10-ms deglitch circuit prevents the  $\overline{OCx}$  signal from oscillation or false triggering. If an overtemperature shutdown occurs, the  $\overline{OCx}$  is asserted instantaneously.



#### **Current Sense**

A sense FET monitors the current supplied to the load. The sense FET measures current more efficiently than conventional resistance methods. When an overload or short circuit is encountered, the current-sense circuitry sends a control signal to the driver. The driver in turn reduces the gate voltage and drives the power FET into its saturation region, which switches the output into a constant-current mode and holds the current constant while varying the voltage on the load.

#### **Thermal Sense**

The TPS206x-1 implements a thermal sensing to monitor the operating temperature of the power distribution switch. In an overcurrent or short-circuit condition the junction temperature rises. When the die temperature rises to approximately 140°C due to overcurrent conditions, the internal thermal sense circuitry turns off the switch, thus preventing the device from damage. Hysteresis is built into the thermal sense, and after the device has cooled approximately 10 degrees, the switch turns back on. The switch continues to cycle off and on until the fault is removed. The open-drain false reporting output (OCx) is asserted (active low) when an overtemperature shutdown or overcurrent occurs.

### **Undervoltage Lockout**

A voltage sense circuit monitors the input voltage. When the input voltage is below approximately 2 V, a control signal turns off the power switch.

### **Discharge Function**

When the device is disabled (when enable is deasserted or during power-up power-down when  $V_1 < UVLO$ ) the discharge function is active. The discharge function offers a resistive discharge path for the external storage capacitor. This is suitable only to discharge filter capacitors for limited time and cannot dissipate steady state currents greater than 8 ma.







#### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
TPS2062D-1	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2062D-1G4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2062DR-1	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2062DR-1G4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2065DGN-1	ACTIVE	MSOP- Power PAD	DGN	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2065DGN-1G4	ACTIVE	MSOP- Power PAD	DGN	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2065DGNR-1	ACTIVE	MSOP- Power PAD	DGN	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2065DGNR-1G4	ACTIVE	MSOP- Power PAD	DGN	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2066DGN-1	ACTIVE	MSOP- Power PAD	DGN	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2066DGN-1G4	ACTIVE	MSOP- Power PAD	DGN	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2066DGNR-1	ACTIVE	MSOP- Power PAD	DGN	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS2066DGNR-1G4	ACTIVE	MSOP- Power PAD	DGN	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

<sup>&</sup>lt;sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder



## PACKAGE OPTION ADDENDUM

27-Feb-2009

temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

# PACKAGE MATERIALS INFORMATION

www.ti.com 18-Jul-2011

## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

Reel Width (W1)

## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS2062DR-1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TPS2065DGNR-1	MSOP- Power PAD	DGN	8	2500	330.0	12.4	5.3	3.3	1.3	8.0	12.0	Q1
TPS2066DGNR-1	MSOP- Power PAD	DGN	8	2500	330.0	12.4	5.3	3.3	1.3	8.0	12.0	Q1

www.ti.com 18-Jul-2011



\*All dimensions are nominal

7 th difficition and from that							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS2062DR-1	SOIC	D	8	2500	340.5	338.1	20.6
TPS2065DGNR-1	MSOP-PowerPAD	DGN	8	2500	346.0	346.0	35.0
TPS2066DGNR-1	MSOP-PowerPAD	DGN	8	2500	346.0	346.0	35.0

DGN (S-PDSO-G8)

# PowerPAD™ PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <a href="https://www.ti.com">www.ti.com</a>.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F. Falls within JEDEC MO-187 variation AA-T

#### PowerPAD is a trademark of Texas Instruments.



# DGN (S-PDSO-G8)

# PowerPAD™ PLASTIC SMALL OUTLINE

#### THERMAL INFORMATION

This PowerPAD  $^{\text{M}}$  package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Exposed Thermal Pad Dimensions

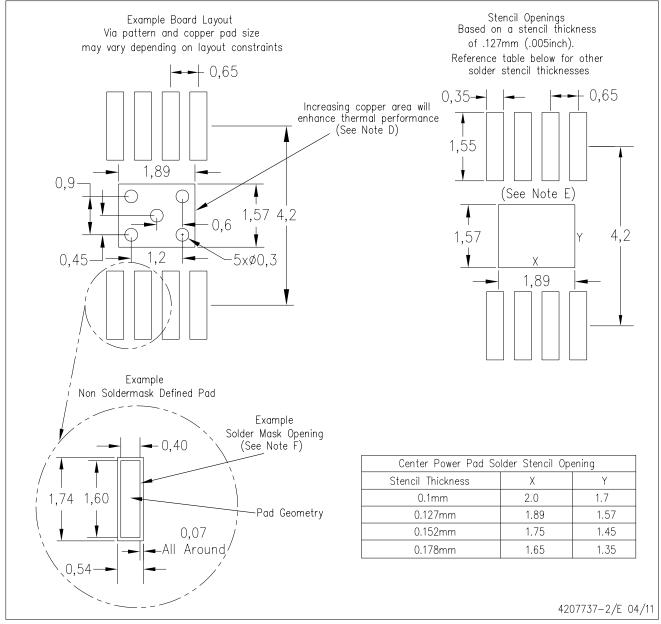
4206323-2/1 12/11

NOTE: All linear dimensions are in millimeters



# DGN (R-PDSO-G8)

# PowerPADTM PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="https://www.ti.com">www.ti.com</a>. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

### PowerPAD is a trademark of Texas Instruments



# DGN (S-PDSO-G8)

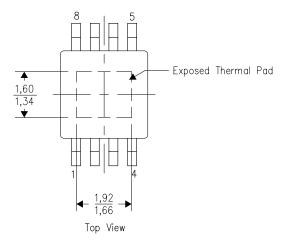
# PowerPAD™ PLASTIC SMALL OUTLINE

#### THERMAL INFORMATION

This PowerPAD  $^{\text{M}}$  package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Exposed Thermal Pad Dimensions

4206323-4/1 12/11

NOTE: All linear dimensions are in millimeters



# D (R-PDSO-G8)

## PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



# D (R-PDSO-G8)

# PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



#### IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46C and to discontinue any product or service per JESD48B. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have not been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components which meet ISO/TS16949 requirements, mainly for automotive use. Components which have not been so designated are neither designed nor intended for automotive use; and TI will not be responsible for any failure of such components to meet such requirements.

www.ti.com/communications

www.ti.com/consumer-apps

www.ti.com/computers

www.ti.com/energy

www.ti.com/industrial

www.ti.com/medical

www.ti.com/security

Products		Applications
Audia	ununu ti com/ou dio	Automotivo on

Wireless Connectivity

Audio Automotive and Transportation www.ti.com/automotive www.ti.com/audio **Amplifiers** amplifier.ti.com Communications and Telecom **Data Converters** dataconverter.ti.com Computers and Peripherals **DLP® Products** Consumer Electronics www.dlp.com DSP dsp.ti.com **Energy and Lighting** Clocks and Timers www.ti.com/clocks Industrial Interface interface.ti.com Medical Logic logic.ti.com Security Power Mgmt Space, Avionics and Defense power.ti.com

www.ti.com/wirelessconnectivity

www.ti.com/space-avionics-defense Microcontrollers microcontroller.ti.com Video and Imaging www.ti.com/video

www.ti-rfid.com

**OMAP Mobile Processors** www.ti.com/omap **TI E2E Community** e2e.ti.com